AMENDMENTS TO THE CLAIMS

1. (currently amended) A device for electrical contacting or for the isolation of organic or inorganic semiconductors in electronic or optoelectric devices comprising

a substrate, either in the form of

- a) a contact material consisting of an organic or inorganic electrical conductor, or
- b) an isolating material consisting of an organic or inorganic dielectric; and

is on or at a surface of the substrate and which forms a charge transfer complex with an organic or inorganic semiconductor,

wherein the charge transfer material

- a) comprises charge transfer components in the form of donors or acceptors,
- b) forms a self-assembling layer of one or more atomic and/or molecular layers,
- c) has a direct or indirect bond to the surface of the substrate, and
- d) forms a charge transfer complex with an organic or inorganic semiconductor, wherein the charge transfer material
 - <u>d)</u> forms a donor <u>material</u> in the charge transfer complex if the semiconductor is an acceptor or <u>forms an</u> acceptor material in the charge transfer complex depending

upon respectively whether <u>if</u> the semiconductor itself is <u>a</u> an acceptor or donor material.

- (previously presented) A device according to claim
 wherein the bond to the surface of the substrate is a chemical or electrostatic bond or a combination thereof.
- 3. (previously presented) A device according to claim 1, wherein the charge transfer material is an organic compound.
- 4. (previously presented) A device according to claim 1, wherein the organic compound comprises a functional group which forms the bond to the surface of the substrate.
- 5. (previously presented) A device according to claim 4, wherein the functional group is material selective and forms the bond to a specific substrate material.
- 6. (previously presented) A device according to claim 1, wherein the charge transfer material is provided at the surface of the substrate and the device further comprises a connection layer without charge transfer components provided between the surface of the substrate and the charge transfer material, wherein the connection layer forms a bond to the

surface of the substrate and a bond to the charge transfer material.

- 7. (previously presented) A device according to claim 6, wherein the bonds of the connection layer each is a chemical or electrostatic bond or a combination thereof.
- 8. (previously presented) A device according to claim 6, wherein the connection layer is formed of an organic bonding agent.
- 9. (previously presented) A device according to claim 8, wherein the organic bonding agent is formed of DNA molecules, such that the one half strand of a DNA molecule is bonded to the surface of a substrate and the complementary second half strand of the DNA molecule is bonded to the charge transfer material.
- 10. (previously presented) A device according to claim 1, wherein the charge transfer material is an atomic or molecular inorganic compound.
- 11. (previously presented) A device according to claim 10, wherein the charge transfer inorganic compound is provided on the surface of the substrate and is formed of a material which reacts chemically with the substrate and which

forms a connection layer consisting of a chemical compound of the substrate material and the inorganic compound between the substrate and the inorganic compound.

- 12. (previously presented) A device according to claim 10, wherein the charge transfer inorganic compound is provided at the surface of the substrate and the device further comprises a connection layer provided between the substrate and the inorganic compound, wherein the connection layer comprises a chemical compound of the substrate material or a material with similar chemical properties, and the charge transfer inorganic compound.
- 13. (previously presented) A method for fabricating a device of claim 1 which comprises

providing a charge transfer material as a patterned or unpatterned self-assembling layer of one or more atomic or molecular layers on or at a surface of the substrate, wherein the charge transfer material includes charge transfer components in the form of donors and/or acceptors,

forming a direct or indirect bond between the charge transfer material and the surface of the substrate,

and forming a charge transfer complex of the charge transfer material together with a thereabove adjacently provided organic or inorganic semiconductor, wherein the charge transfer material forms a donor or acceptor material

in the charge transfer complex depending upon respectively whether the semiconductor itself is an acceptor or donor material.

- 14. (previously presented) A method according to claim 13, which further comprises forming the bond as a chemical or electrostatic bond or a combination thereof.
- 15. (previously presented) A method according to claim
 13, which further comprises selecting the charge transfer
 material as an organic compound.
- 16. (previously presented) A method according to claim 15, which further comprises selecting the organic compound with a functional group which forms the bond to the surface of the substrate.
- 17. (previously presented) A method according to claim 16, which further comprises selecting the functional group as a material-selective group such that the bond is formed to a specific substrate material.
- 18. (previously presented) A method according to claim 13, wherein the charge transfer material is provided at the surface of the substrate, and which further comprises providing a connection layer without charge transfer

components between the surface of the substrate and the charge transfer material, and forming the connection layer with a bond to the surface of the substrate and with a bond to the charge transfer material.

- 19. (previously presented) A method according to claim 18, which further comprises forming each bond in the connection layer as a chemical or electrostatic bond or a combination thereof.
- 20. (previously presented) A method according to claim 18, which further comprises forming the connection layer of an organic bonding agent.
- 21. (previously presented) A method according to claim 20, which further comprises forming the organic bonding agent of DNA molecules, such that the one half strand of a DNA molecule is bond to the surface of the substrate and the complementary second half strand of the DNA molecule is bond to the charge transfer material.
- 22. (previously presented) A method according to claim 13, which further comprises selecting the charge transfer material as an atomic or molecular inorganic compound.

- 23. (previously presented) A method according to claim 22, wherein the charge transfer inorganic compound is provided on the surface of the substrate, and which further comprises forming the inorganic compound of a material which reacts chemically with the substrate such that between the substrate and the inorganic compound a connection layer consisting of a chemical compound of the substrate material and the inorganic compound is formed.
- 24. (previously presented) A method according to claim 22, wherein the charge transfer inorganic compound is provided at the surface of the substrate, and which further comprises providing a connection layer consisting of a compound of the substrate material or a material with similar chemical properties, and the inorganic compound, between the substrate and the inorganic compound.
- 25. (currently amended) A device for electrical contacting or for the isolation of organic or inorganic semiconductors in electronic or optoelectric devices comprising
 - a substrate, either in the form of
 - a) a contact material consisting of an organic or inorganic electrical conductor, or
 - b) an isolating material consisting of an organic or inorganic dielectric; and

is on or at a surface of the substrate and which forms a charge transfer complex with an organic or inorganic semiconductor.

wherein the charge transfer material

- a) comprises charge transfer components in the form of donors or acceptors,
- b) forms a self-assembling layer of one or more atomic or molecular layers,
- c) has a direct or indirect bond to the surface of the substrate,
- d) forms a charge transfer complex with an organic or inorganic semiconductor, wherein the charge transfer material
 - <u>d)</u> forms a donor <u>material</u> in the charge transfer complex if the semiconductor is an acceptor or forms an acceptor material in the charge transfer complex depending upon respectively whether <u>if</u> the semiconductor <u>itself</u> is <u>a</u> an acceptor or donor material, and
 - e) is made from inorganic charge transfer compound or an organic charge transfer compound selected from the group consisting of

wherein R is F, Cl or NO_2 and X is -NC or SH.